



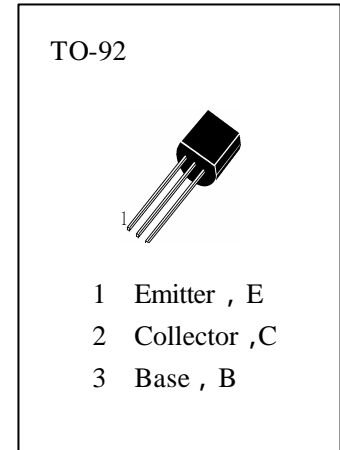
H4204

APPLICATIONS

AF Amplifier , Various Drivers.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation.....	600mW
V_{CBO}	Collector-Base Voltage.....	30V
V_{CEO}	Collector-Emitter Voltage.....	25V
V_{EBO}	Emitter-Base Voltage.....	15V
I_C	Collector Current.....	700mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	30			V	$I_C=10 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	25			V	$I_C=1mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	15			V	$I_E=10 \mu A, I_C=0$
HFE(1)	DC Current Gain	800	1500	3200		$V_{CE}=5V, I_C=50mA$
HFE(2)	DC Current Gain	600				$V_{CE}=5V, I_C=500mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		0.15	0.5	V	$I_C=500mA, I_B=10mA$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		0.9	1.2	V	$I_C=500mA, I_B=10mA$
ICBO	Collector Cut-off Current			100	nA	$V_{CB}=20V, I_E=0$
IEBO	Emitter Cut-off Current			100	nA	$V_{EB}=10V, I_C=0$
ft	Current Gain-Bandwidth Product		270		MHz	$V_{CE}=10V, I_C=50mA$,
Cob	Output Capacitance		9		pF	$V_{CB}=10V, f=1MHz$
tON	Turn-On Time		0.1		μS	See specified test circuit
tSTG	Storage Time		0.6		μS	See specified test circuit
tF	Fall Time		0.06		μS	See specified test circuit

